

Title (en)

FORMING A SEMICONDUCTOR STRUCTURE USING A COMBINATION OF PLANARIZING METHODS AND ELECTROPOLISHING

Title (de)

BILDUNG EINER HALBLEITERSTRUKTUR UNTER VERWENDUNG EINER KOMBINATION VON PLANARISIERUNGSVERFAHREN UND ELEKTROPOLIEREN

Title (fr)

FORMATION D'UNE STRUCTURE A SEMI-CONDUCTEUR AU MOYEN D'UNE COMBINAISON DE PROCEDE DE PLANARISATION ET DE POLISSAGE ELECTROLYTIQUE

Publication

EP 1423868 A2 20040602 (EN)

Application

EP 02773205 A 20020815

Priority

- US 0226167 W 20020815
- US 31308601 P 20010817

Abstract (en)

[origin: WO03017330A2] A method for planarizing and electropolishing a conductive layer on a semiconductor structure includes forming a dielectric layer with recessed areas and non-recessed areas on the semiconductor wafer. A conductive layer is formed over the dielectric layer to cover the recessed areas and non-recessed areas. The surface of the conductive layer is then planarized to reduce variations in the topology of the surface. The planarized conductive layer is then electropolished to expose the non-recessed area.

IPC 1-7

H01L 21/302

IPC 8 full level

C25F 3/22 (2006.01); **B23H 5/08** (2006.01); **B24B 37/04** (2012.01); **C25F 3/16** (2006.01); **C25F 3/30** (2006.01); **H01L 21/304** (2006.01); **H01L 21/3205** (2006.01); **H01L 21/321** (2006.01); **H01L 21/3213** (2006.01); **H01L 21/768** (2006.01)

CPC (source: EP KR)

B23H 5/08 (2013.01 - EP); **B24B 37/04** (2013.01 - EP); **C25F 3/16** (2013.01 - EP); **H01L 21/302** (2013.01 - KR); **H01L 21/32115** (2013.01 - EP); **H01L 21/3212** (2013.01 - EP); **H01L 21/32134** (2013.01 - EP); **H01L 21/32136** (2013.01 - EP); **H01L 21/7684** (2013.01 - EP); **H01L 2924/0002** (2013.01 - EP)

Citation (search report)

See references of WO 03017330A2

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR IE IT LI LU MC NL PT SE SK TR

DOCDB simple family (publication)

WO 03017330 A2 20030227; **WO 03017330 A3 20030724**; AU 2002336360 A1 20030303; CA 2456225 A1 20030227; CN 100419963 C 20080917; CN 1543668 A 20041103; EP 1423868 A2 20040602; JP 2005500687 A 20050106; KR 100899060 B1 20090525; KR 20040030147 A 20040408; TW 569330 B 20040101

DOCDB simple family (application)

US 0226167 W 20020815; AU 2002336360 A 20020815; CA 2456225 A 20020815; CN 02816119 A 20020815; EP 02773205 A 20020815; JP 2003522140 A 20020815; KR 20047002336 A 20020815; TW 91118584 A 20020816